

/ Descriptions

TO-126F NPN Silicon NPN transistor in a TO-126F Plastic Package.

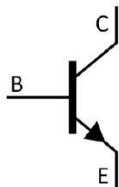
/ Features

2SA886 4W
4W output in complementary pair with 2SA886.

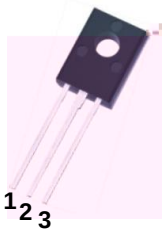
/ Applications

Medium power amplifier.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Collector PIN 3 Base

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	P	Q	R
h_{FE} Range	50 100	80 160	120 220

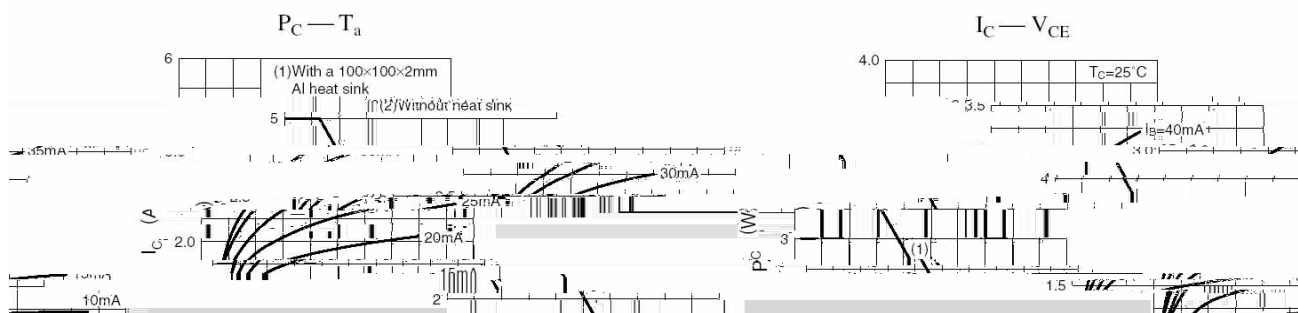
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	40	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	1.5	A
Collector Current – Continuous(Pulse)	I_{CP}	3.0	A
Collector Power Dissipation	P_C	1.2	W
Collector Power Dissipation*	$*P_C(T_C=25^\circ C)$	5.0*	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

* P_C : 100×100×20mm

*With a 100×100×20mm AL heat sink

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=1.0mA$ $I_E=0$	50			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=2.0mA$ $I_B=0$	40			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=20V$ $I_E=0$			1.0	A
Collector Cut-Off Current	I_{CEO}	$V_{CE}=10V$ $I_B=0$			100	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			10	A
	I_{FE}	$V_{CE}=5.0V$ $I_C=$ *5	1			0
V_o	$I_{CE(sat)}$	$V_{CE}=V_{CB}$ $I_B=$ * 0		$\frac{1}{0}$	$\frac{0}{A}$	$\frac{V}{2}$
	T_V	$V_{CE}=5.0V$ $I_C=$	0			5
		$V_{CB}=20V$ $I_E=0$ $f = 1$ M H z				

/ Electrical Characteristic Curve



2SC1847

/ Marking Instructions

